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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of	)	Customer No. 00832
Keiji Ishibashi	)	
Serial No. 09/633,002	)	Group: 1762
Filed: August 4, 2000	)	
Title: A HOT ELEMENT CVD APPARATUS AND A METHOD FOR REMOVING A DEPOSITED FILM	)	Examiner: W. Markham

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Responsive to the Office Action dated April 2, 2002, which had a period for response which expired on July 2, 2002, which period has been extended by the enclosed Petition For Extension Of Time (three-month) to expire on October 2, 2002, Applicant hereby submits the following amendment:

IN THE SPECIFICATION:

Please replace the second paragraph on page 9 with the following rewritten paragraph:

C1

The gas ejected from gas outlets 210 is effectively decomposed and/or activated by the platinum of the hot element which is maintained at a high temperature to generate activated species. For example, the hot element is preferably heated at 400°C and 1000°C or higher in the case of employing NF_3 and CF_4 as a cleaning gas, respectively. An activated species that is highly reactive with a deposited film can be generated by the catalytic action of the platinum. The platinum is stable against the activated species. Therefore, the stable film formation can be carried out even after the cleaning treatment. The activated species reacts with the films deposited on the surface of the inner wall, the substrate holder and the like and converts the films into gaseous substances. The films are gradually removed as the gaseous substances thus generated are evacuated outside by the exhaust system.